

MICRO ELECTRONICS

PN3565

PNP
SILICON
TRANSISTOR

DESCRIPTION

PN3565 is PNP silicon planar transistor designed for AF small signal amplifier stages.

TO-92A



EBC

ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	V _{CEO}	25V
Collector-Base Voltage	V _{CB0}	30V
Emitter-Base Voltage	V _{EB0}	6V
Collector Current	I _C	50mA
Continuous Power Dissipation	P _d	300mW
Operating & Storage Junction Temperature	T _j , T _{stg}	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS (T_a=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS
Collector-Emitter Breakdown Voltage	LV _{CEO}	25		V	I _C =2mA IB=0
Collector-Base Breakdown Voltage	BV _{CB0}	30		V	I _C =100μA IE=0
Emitter-Base Breakdown Voltage	BV _{EB0}	6		V	IE=10μA IC=0
Collector Cutoff Current	IC _{BO}		50	nA	VCB=25V IE=0
Emitter Cutoff Current	IE _{BO}		100	nA	VEB=3V IC=0
D.C. Current Gain	HFE	150	600		I _C =1mA VCE=10V
	HFE	70			I _C =100μA VCE=10V
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.35	V	I _C =1mA IB=0.1mA
Current Gain Bandwidth Product	f _T	40		MHz	I _C =1mA VCE=5V
Output Capacitance	C _{ob}		4	pF	VCB=5V f=1MHz

* Pulse test : pulse width < 300μS, duty cycle < 2%.



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